TO-252 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a TO-252 Plastic Package.

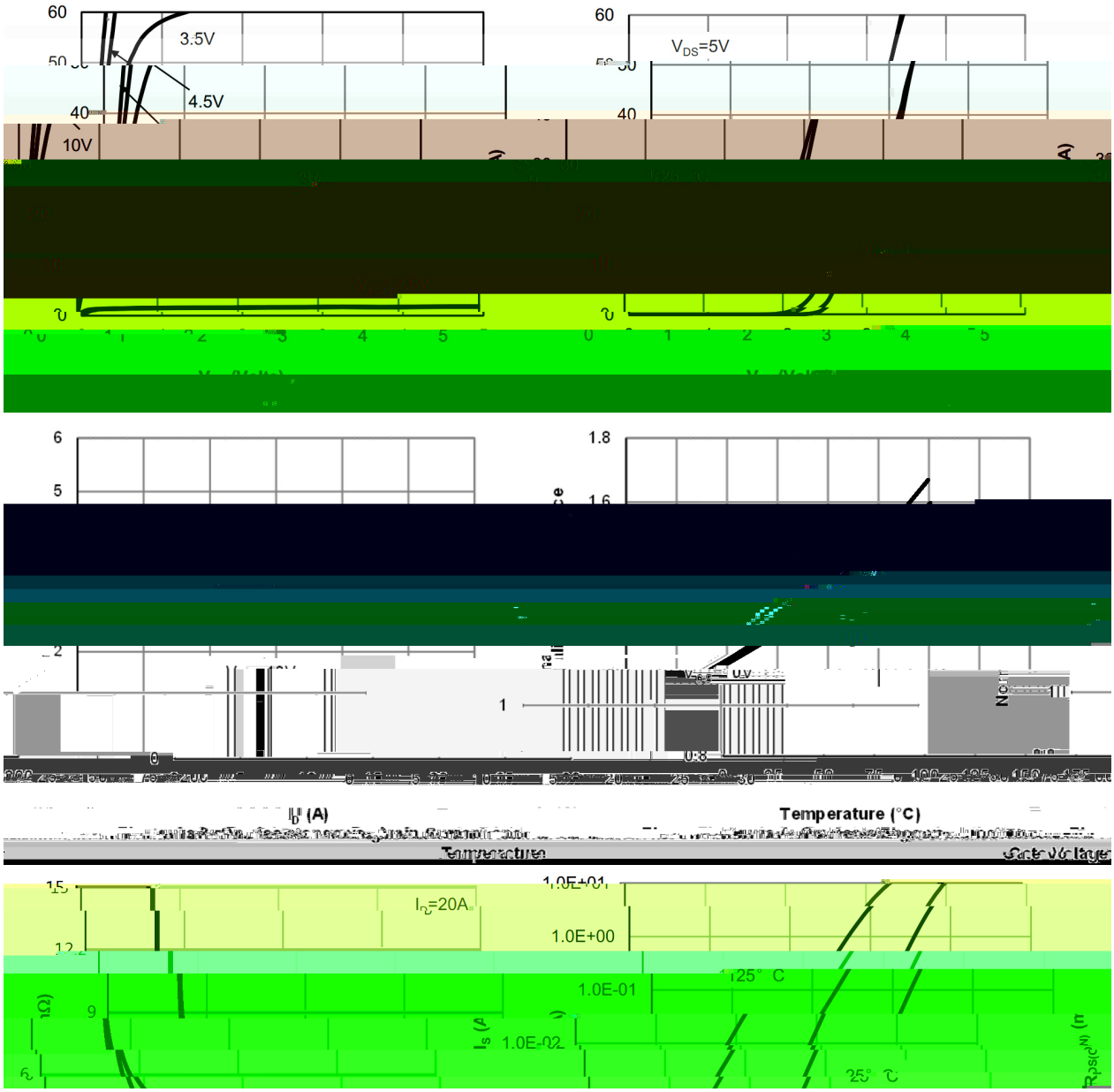
V_{DS} (V) = 30V I

Parameter

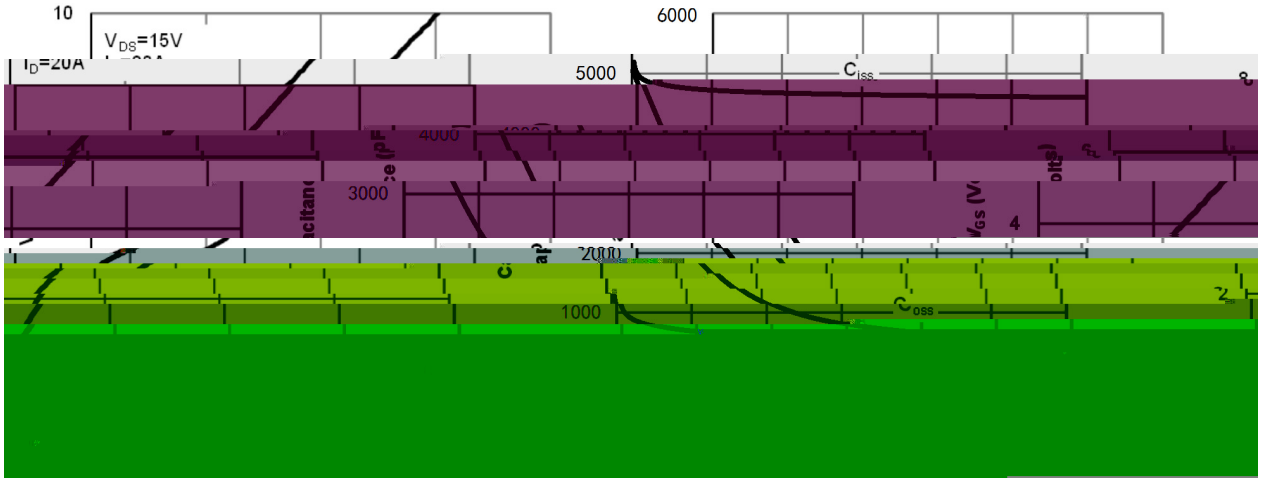
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V V_{DS}=15V I_D=20A		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			5.2		
Gate Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=15V R_L=0.75Ω R_{GEN}=3Ω		8.5		ns
Turn-On Rise Time	t_r			4.2		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			5.7		

/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



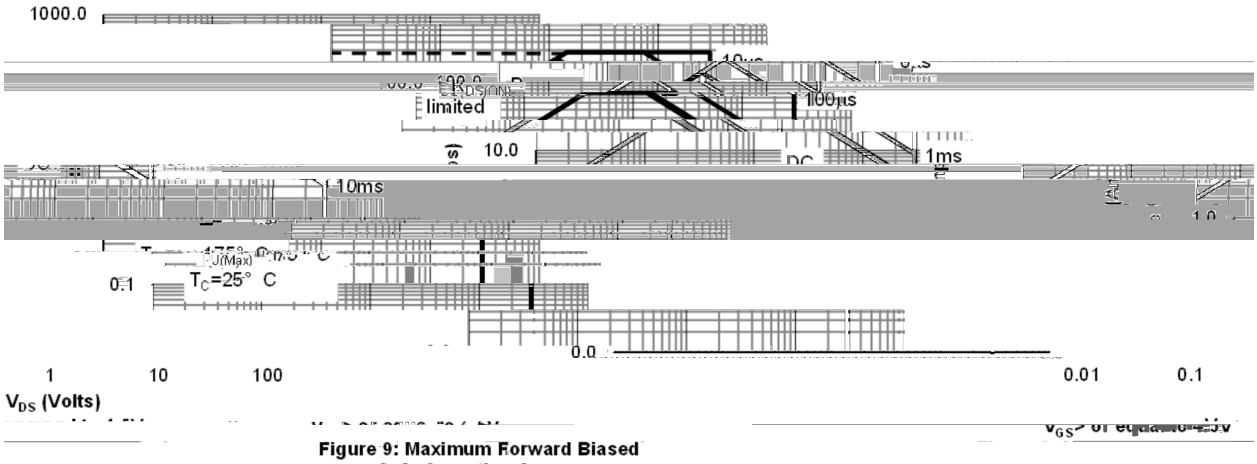
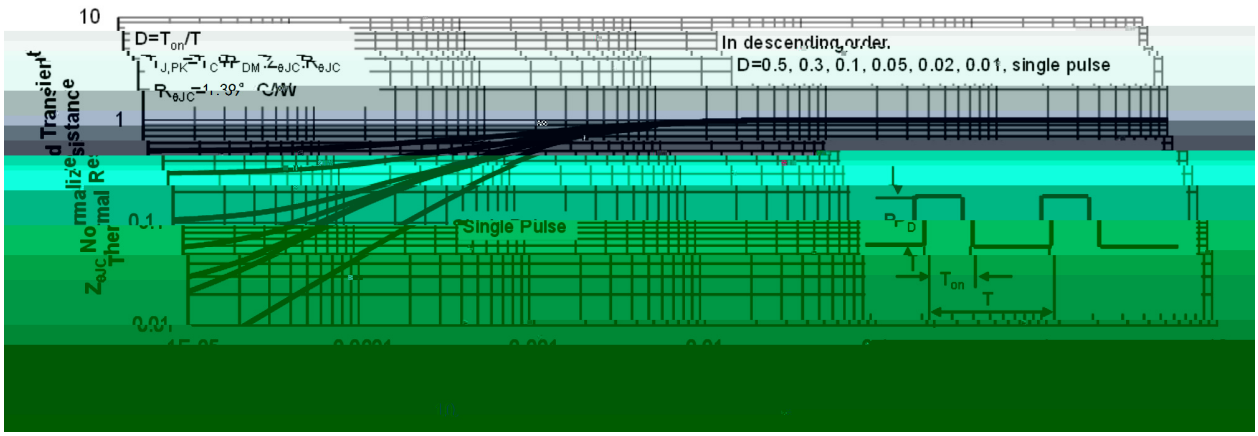
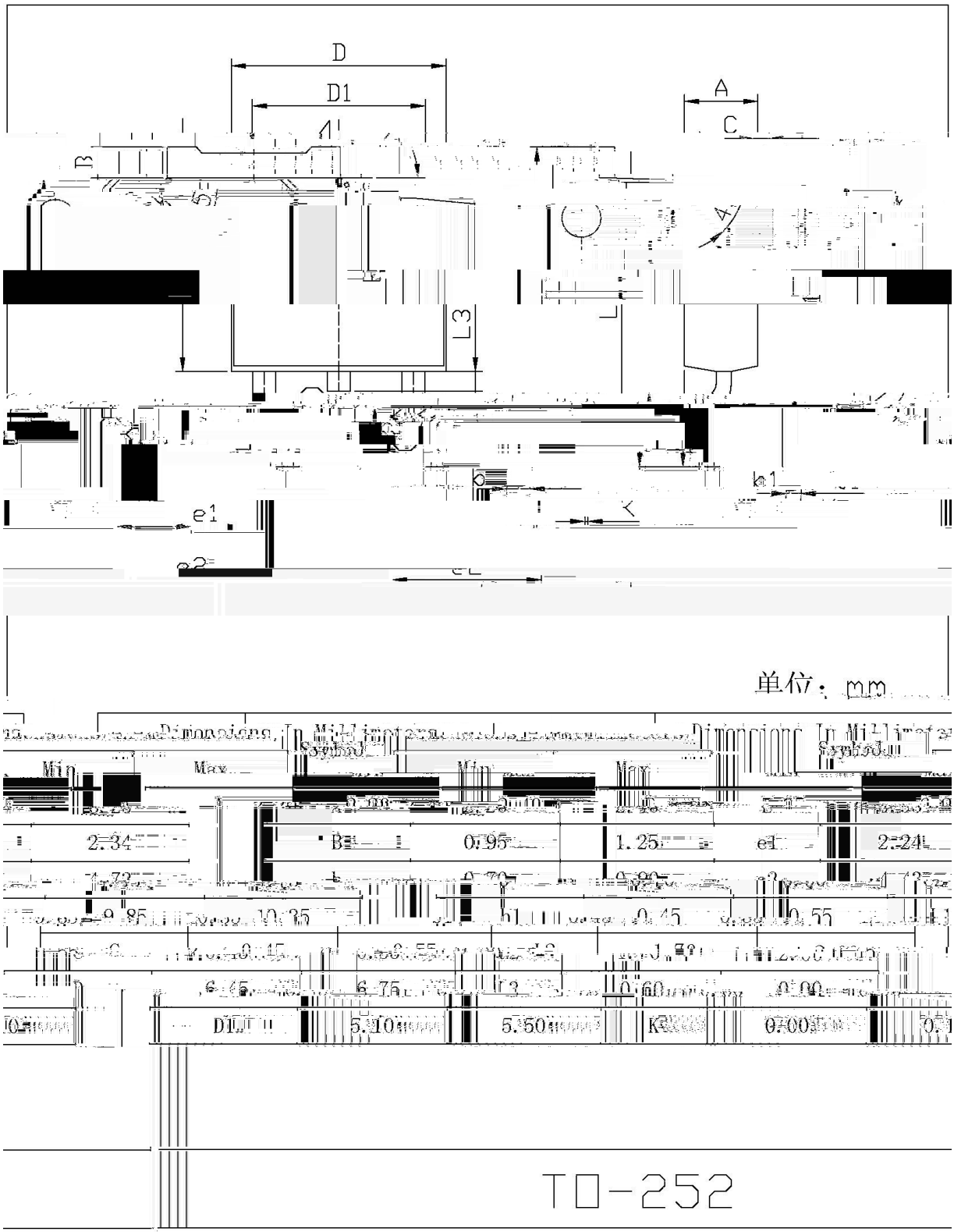


Figure 9: Maximum Forward Biased



/ Package Dimensions



/ Marking Instructions

